

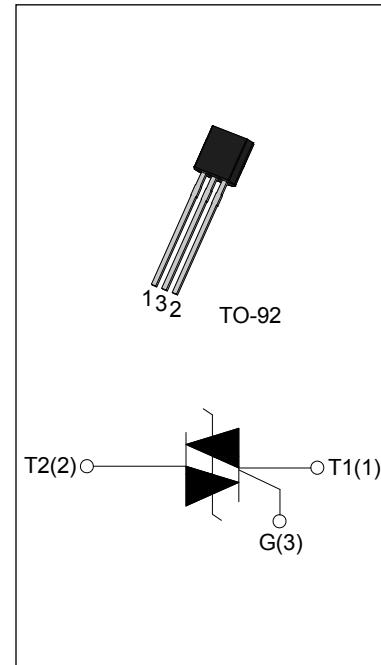


ACJT1U 1A TRIACs

Rev.8.0

DESCRIPTION:

ACJT1U triacs with high ability to withstand the shock loading of large current provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on inductive load and serious electromagnetic interference place. Package TO-92 is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	600/800/1000	V
I_{GT}	≤ 5 or ≤ 10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ C$)	V_{DRM}	600/800/1000	V
Repetitive peak reverse voltage($T_j=25^\circ C$)	V_{RRM}	600/800/1000	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current TO-92 ($T_c=50^\circ C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $F=50Hz$)	I_{TSM}	10	A
I^2t value for fusing ($tp=10ms$)	I^2t	1.12	A^2s
Rate of rise of on-state current ($I_G=2\times I_{GT}$)	dI_T/dt	50	$A/\mu s$
Peak gate current	I_{GM}	1	A
Average gate power dissipation	$P_{G(AV)}$	0.2	W
Peak gate power	P_{GM}	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				ACJT105	ACJT110	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX	5	10	mA
V_{GT}		I - II -III	MAX	1.3		V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	15	25	mA
		II		25	35	
I_H	$I_T=100\text{mA}$		MAX	10	20	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	400	600	V/ μ s

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=1.4\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5
I_{DRM}	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5
I_{RRM}			$T_j=125^\circ\text{C}$	0.5

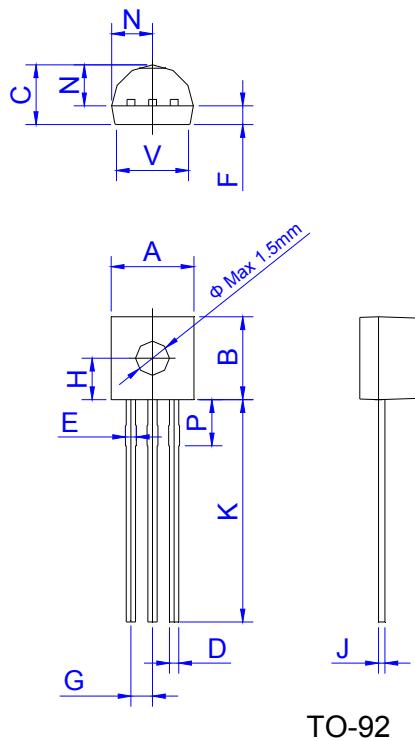
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-92	60	°C/W

ORDERING INFORMATION

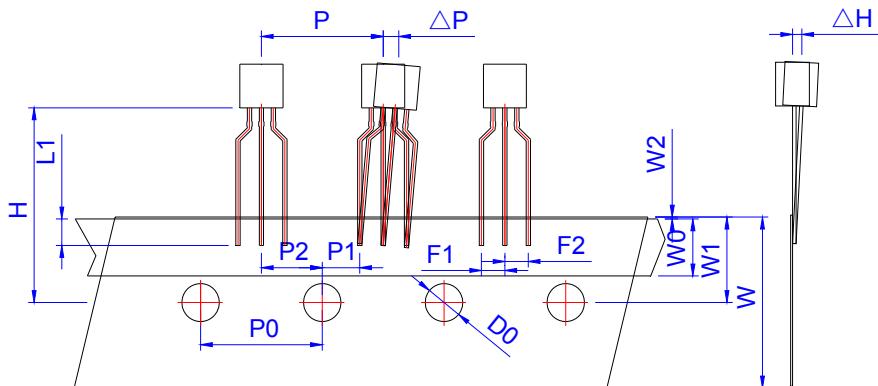
AC	J	T	1	05	-6	U	-TR
AC switch JieJie Microelectronics Co.,Ltd							
		Triacs					
			IT(RMS):1A				
						U:TO-92	TR: Tape & Reel Blank: Ammopack
							6: $V_{DRM} \wedge V_{RRM} \geq 600\text{V}$
							8: $V_{DRM} \wedge V_{RRM} \geq 800\text{V}$
							10: $V_{DRM} \wedge V_{RRM} \geq 1000\text{V}$

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

INFORMATION OF TAPE & REEL - TO-92

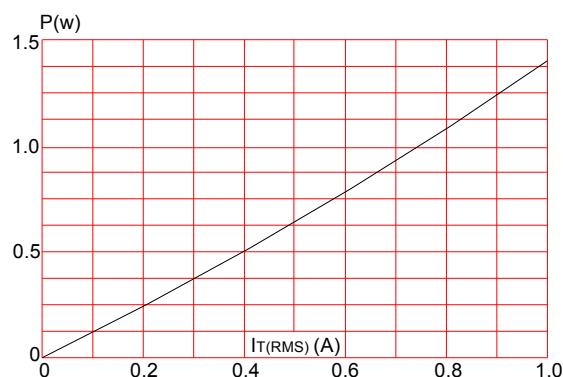
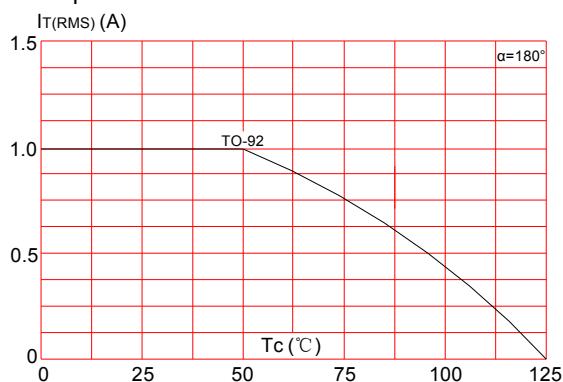
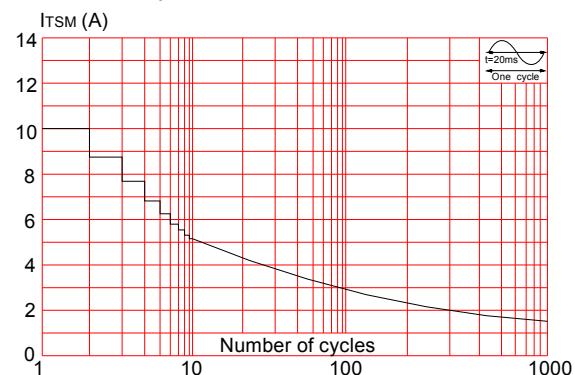
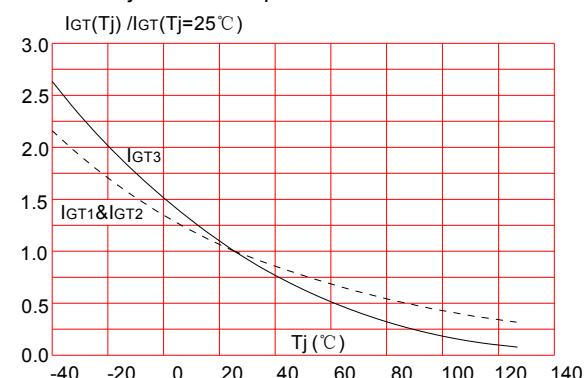
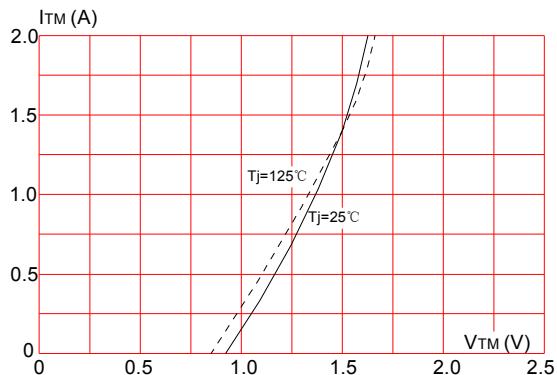
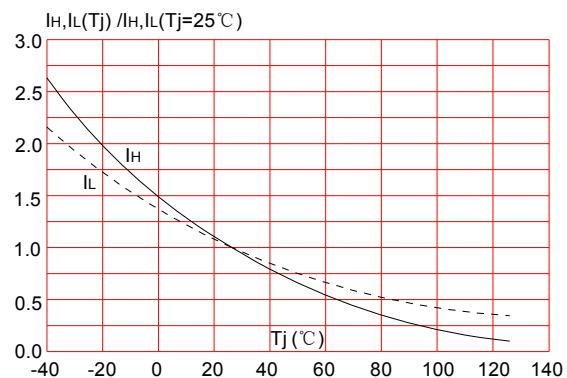


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	6.05	6.35	6.65	0.238	0.250	0.262
ΔP	-1.0	0	1.0	-0.039	0	0.039
F1、F2	2.20	2.50	2.80	0.087	0.098	0.110
F1-F2	-0.3	0	0.3	-0.012	0	0.012
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.0			0.039
D0	3.80	4.0	4.20	0.150	0.157	0.165
ΔH	-1.0	0	1.0	-0.039	0	0.039
L1	2.5			0.098		
H	18.0	19.0	20.0	0.709	0.748	0.787

Packaging Information	Reel	Inner Box	Outer Box
Net Weight (g)	140	80	600
Quantity (pcs)	/	2000	20000
N. W. Per Unit (mg/pcs)	189		

PACKAGE INFORMATION

PACKAGE	WEIGHT (PER PCS)	OUTLINE	BAG (PCS)	INNER BOX (PCS)	PER CARTON
TO-92	0.1894g	Ammopack	1,000	10,000	50,000
PACKAGE	WEIGHT (PER PCS)	OUTLINE	REEL	INNER BOX (PCS)	PER CARTON
TO-92	0.1894g	Tape & Reel	2,000	2,000	20,000

FIG.1 Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Relative variations of gate trigger current versus junction temperature**FIG.4:** On-state characteristics (maximum values)**FIG.6:** Relative variations of holding current, latching current versus junction temperature

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